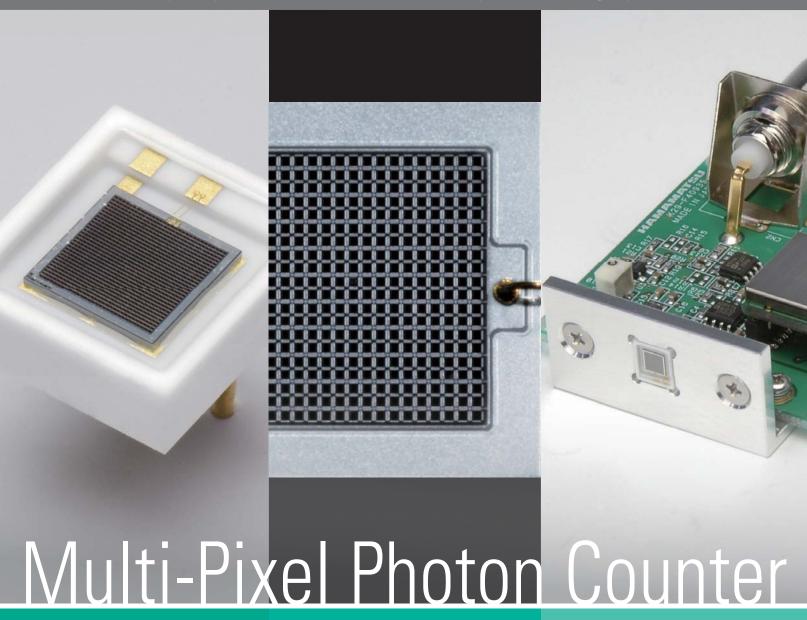


# MPPC® Modules

Compact opto-semiconductors with excellent photon-counting capability





# MPPC Modules

New type of Si photon-counting device

The MPPC (multi-pixel photon counter) is a new type of photon-counting device made up of multiple APD (avalanche photodiode) pixels operated in Geiger mode. The MPPC is essentially an opto-semiconductor device with excellent photon-counting capability and which also possesses great advantages such as low voltage operation and insensitivity to magnetic fields.

#### Features

- Excellent photon-counting capability
   (excellent detection efficiency versus number of incident photons)
- · Small size
- · Room temperature operation
- · Low bias (below 80 V) operation
- · High gain: 105 to 106
- . Excellent time resolution
- · Insensitive to magnetic fields
- · Simple readout circuit operation
- · MPPC module available



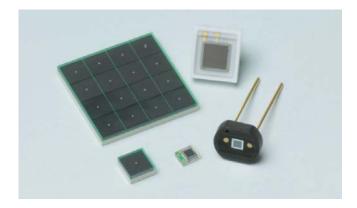
# **Contents**

MPPC · · · · · · · · · · · · · · · · · ·	3
· Hamamatsu MPPC· · · ·	3
· MPPC lineup· · · · · · · ·	7
· MPPC for general meas	surement 9



· High-speed, wide dynamic range MPPC · · · · · 13	· Application examples of MPPC modules · · · · · 24
· MPPC for very low light level measurement · · · 17	· Analog output type MPPC modules · · · · · · · 25
■ MPPC modules · · · · · · 19	· Digital output type MPPC modules · · · · · · · 28
· MPPC module lineup · · · · · · · · · 23	· Starter kits · · · · · · · 30

# Hamamatsu MPPC



# Operating principle

#### Photon counting

Light has the properties of both a particle and a wave. When the light level becomes extremely low, light behaves as discrete particles (photons) allowing us to count the number of photons. Photon counting is a technique for measuring the number of individual photons.

The MPPC is suitable for photon counting since it offers excellent time resolution and a multiplication function having high gain and low noise. Compared to ordinary light measurement techniques that measure the output current as analog signals, photon counting delivers a higher S/N and higher stability even in measurements at very low light levels.

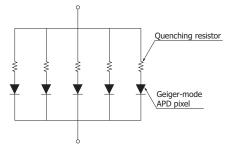
## Geiger mode and quenching

When the reverse voltage applied to an APD is set higher than the breakdown voltage, the electric field in the APD becomes high enough to cause a discharge (Geiger discharge) even by input of very weak light. The condition where an APD operates at this voltage level is called Geiger mode. Geiger mode allows obtaining a large output by way of the discharge even when detecting a single photon. Once Geiger discharge begins, it continues for as long as the electric field in the APD is maintained. To halt a Geiger discharge and detect the next photon, an external circuit outside the APD must lower the operating voltage. One specific example for halting Geiger discharge is a technique using a so-called quenching resistor connected in series with the APD. This guickly stops avalanche multiplication in the APD because a drop in the operating voltage occurs when the output current caused by the Geiger discharge flows in the quenching resistor. The output current caused by Geiger discharge is a pulse waveform with a sharp rise time, while the output current when Geiger discharge is halted by the quenching resistor is a pulse waveform with a relatively slow fall time.

#### Structure

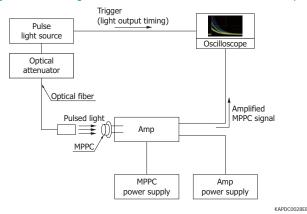
Figure 1 shows a structure of an MPPC. The basic element (pixel) of an MPPC is a combination of Geiger mode APD and quenching resistor, and a large number of these pixels are electrically connected and arranged in two dimensions.

#### [Figure 1] Structure

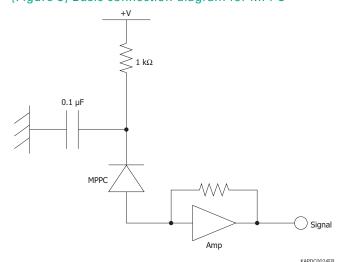


KAPDC0029EA

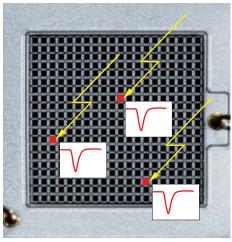
[Figure 2] Block diagram for MPPC evaluation (with an oscilloscope)



[Figure 3] Basic connection diagram for MPPC



[Figure 4] Image of MPPC's photon counting



KAPDC0049EA

#### Basic operation

Each pixel in the MPPC outputs a pulse at the same amplitude when it detects a photon. Pulses generated by multiple pixels are output while superimposed onto each other. For example, if four photons are incident on different pixels and detected at the same time, then the MPPC outputs a signal whose amplitude equals the height of the four superimposed pulses.

Each pixel outputs only one pulse and this does not vary with the number of incident photons. So the number of output pulses is always one regardless of whether one photon or two or more photons enter a pixel at the same time. This means that MPPC output linearity gets worse as more photons are incident on the MPPC such as when two or more photons enter one pixel. This makes it essential to select an MPPC having enough pixels to match the number of incident photons.

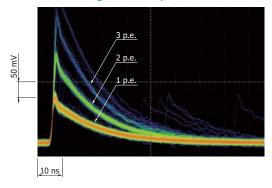
The following two methods are used to estimate the number of photons detected by the MPPC.

- (1) Observing the pulse
- (2) Integrating the output charge

#### (1) Observing the pulse

When light enters an MPPC at a particular timing, its output pulse height varies depending on the number of photons detected. Figure 5 shows output pulses from the MPPC obtained when it was illuminated with pulsed light at photon counting levels and then amplified with a linear amplifier and observed on an oscilloscope. As can be seen from the figure, the pulses are separate from each other according to the number of detected photons such as one, two, three photons and so on. Measuring the height of each pulse allows estimating the number of detected photons.

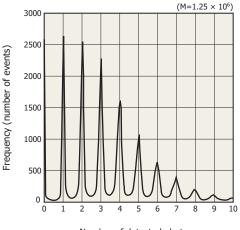
[Figure 5] Pulse waveforms (S12571-050C, M=1.25  $\times$  10<sup>6</sup>) when using linear amplifier (120 times)



#### (2) Integrating the output charge

When the timing at which light enters an MPPC is different, the number of photons detected within a certain time period can be estimated by integrating the MPPC output using an integrating amplifier or similar device. Figure 6 shows the distribution plotted for the amount of charge accumulated in the integration time. Each peak from the left corresponds to the pedestal, one photon, two photons, three photons and so on. Since the MPPC gain is high enough to produce a large amount of charge, the distribution can show discrete peaks according to the number of detected photons.

[Figure 6] Pulse height spectrum when using charge amplifier (S12571-050C, M=1.25  $\times$  10<sup>6</sup>)



Number of detected photons

KAPDB0133FA

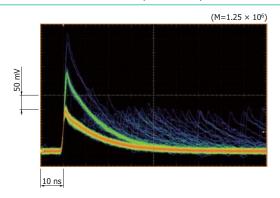
Features

# Low afterpulse

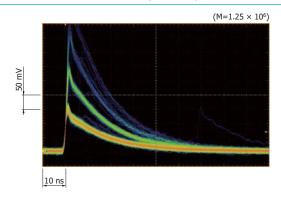
When an MPPC detects photons, the output may contain spurious signals appearing with a time delay from the light input to the MPPC. These signals are called afterpulses. Compared to our previously marketed products, all MPPCs listed in this catalog have drastically reduced afterpulses due to use of improved materials and wafer process technologies. Reducing afterpulses brings various benefits such as a better S/N, a wider operating voltage range, and improved time resolution and photon detection efficiency in high voltage regions.

[Figure 7] Pulse waveforms

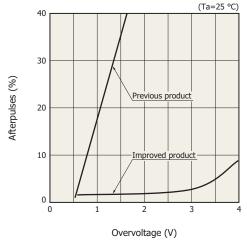
#### S10362-11-050C (previous product)



#### S12571-050C (improved product)



[Figure 8] Afterpulses vs. overvoltage (typical example)



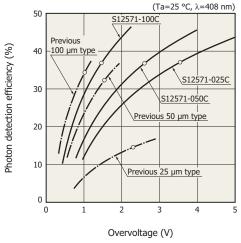
KAPDB0256EA

## High photon detection efficiency

MPPC has peak sensitivity at a wavelength around 400 to 500 nm. MPPC sensitivity is referred to as photon detection efficiency (PDE) and is calculated by the product of the quantum efficiency, fill factor, and avalanche probability. Among these, the avalanche probability is dependent on the operating voltage. Our 25  $\mu m$  pitch MPPC is designed for a high fill factor that vastly improves photon detection efficiency compared to our previous types. Using this same design, we also developed 10  $\mu m$  and 25  $\mu m$  pitch MPPC that delivers high-speed response and wide dynamic range as well as high photon detection efficiency. The fill factor of 50  $\mu m$  and

100  $\mu m$  pitch MPPC is almost the same as that of previous types because increasing the fill factor also causes a significant rise in crosstalk.

[Figure 9] Photon detection efficiency vs. overvoltage (typical example)



KAPDB0217EA

[Table 1] Recommended overvoltage

Pixel pitch	Recommended overvoltage Vov						
(µm)	Previous type (V)	S12571 series (V)					
25	2.3	3.5					
50	1.5	2.6					
100	1.0	1.4					

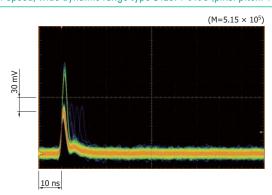
Overvoltage (Vov) = Operating voltage (Vop) – Breakdown voltage (VBR) Photon detection efficiency does not include crosstalk and afterpulses.

#### Wide dynamic range

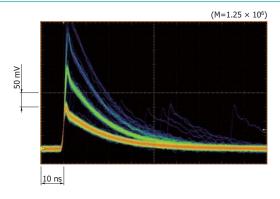
The MPPC dynamic range is determined by the number of pixels and the pixel recovery time. Hamamatsu has developed MPPC with a smallest pixel pitch of 10  $\mu$ m, which increases the number of pixels per unit area and shortens the response time. This drastically extends the MPPC dynamic range.

[Figure 10] Pulse waveforms

High-speed, wide dynamic range type S12571-010C (pixel pitch: 10 µm)



#### General measurement type S12571-050C (pixel pitch: 50 µm)

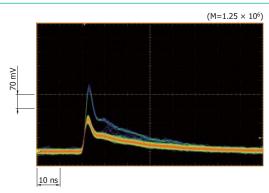


#### Low crosstalk

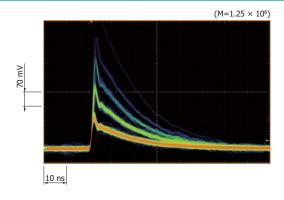
Pixels that detect photons may affect other pixels, making them produce spurious pulses. This phenomenon is called crosstalk. Hamamatsu has drastically reduced crosstalk in precision measurement MPPC by creating barriers between pixels.

[Figure 11] Pulse waveforms

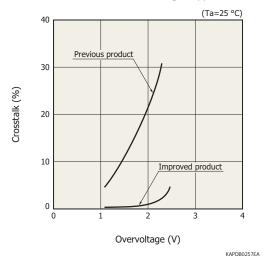
Precision measurement type S12651-050C (pixel pitch:  $50 \mu m$ )



General measurement type S12571-050C (pixel pitch: 50 µm)



[Figure 12] Crosstalk vs. overvoltage (typical example)

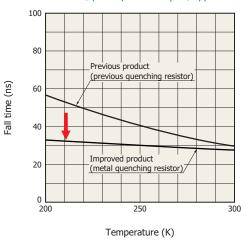


#### Metal quenching resistor

Using a metal quenching resistor has reduced the resistance temperature coefficient to one-fifth of the previous types. This suppresses variations in the fall time in the low temperature region and so improves the output waveforms at low temperatures.

For information on the operating temperature range, refer to the individual datasheets.

[Figure 13] Fall time vs. temperature (photosensitive area: 1 x 1 mm, pixel pitch: 50 µm, typical example)



# **MPPC** lineup

# For general measurement NEW

These MPPCs are suitable for general low-light-level measurement.

Type. no	Previous product	Photosensitive area (mm)	Pixel pitch (µm)	Package	Low dark count	Low afterpulse	High photon detection efficiency	High speed, wide band- width	Low crosstalk	Cooling
S12571-025C	S10362-11-025C		25		0	0	0			
S12571-050C	S10362-11-050C		50	Ceramic	0	0	0			
S12571-100C	S10362-11-100C	11	100		0	0	0			
S12571-025P	S10362-11-025P	1 × 1	25	Surface mount type	0	0	0			
S12571-050P	S10362-11-050P	1	50		0	0	0			
S12571-100P	S10362-11-100P	]	100		0	0	0			
S12572-025C	S10362-33-025C		25		0	0	0			
S12572-050C	S10362-33-050C	]	50	Ceramic	0	0	0			
S12572-100C	S10362-33-100C		100		0	0	0			
S12572-025P	S10931-025P	3 × 3	25		0	0	0			
S12572-050P	S10931-050P	1	50	Surface mount type	0	0	0			
S12572-100P	S10931-100P	1	100	inodin type	0	0	0			

# High-speed, wide dynamic range NEW

This type of MPPC has a large number of pixels, making it suitable for applications where background light may cause saturation.

Type. no	Previous product	Photosensitive area (mm)	Pixel pitch (µm)	Package	Low dark count	Low afterpulse	High photon detection efficiency	High speed, wide band- width	Low crosstalk	Cooling
S12571-010C	-		10	Ceramic	0	0	0	0		
S12571-015C	-	1 × 1	15	Ceramic	0	0	0	0		
S12571-010P	-	1 × 1	10	Surface	0	0	0	0		
S12571-015P	-	1	15	mount type	0	0	0	0		
S12572-010C	-		10	Cararaia	0	0	0	0		
S12572-015C	-	3 × 3	15	Ceramic	0	0	0	0		
S12572-010P	-	] 3×3	10	10 Surface	0	0	0	0		
S12572-015P	-	]	15	mount type	0	0	0	0		

# For very low light level measurement NEW

These MPPCs allow accurate measurements with lower dark count by cooling.

Type. no	Previous product	Photosensitive area (mm)	Pixel pitch (µm)	Package	Low dark count	Low afterpulse	High photon detection efficiency	High speed, wide band- width	Low crosstalk	Cooling
S12576-050	S11028-050	1 × 1	50	Metal	0	0	0			0
S12577-050	-	3 × 3	50	(Two-stage TE-cooled)	0	0	0			0

# For precision measurement Preliminary

This type of MPPC has low crosstalk and decreases counting errors during measurement at low count rates.

Type. no	Previous product	Photosensitive area (mm)	Pixel pitch (µm)	Package	Low dark count	Low afterpulse	High photon detection efficiency	High speed, wide band- width	Low crosstalk	Cooling
S12651-050C	S10362-11-050C	1 × 1	50		0	0			0	
S12651-100C	S10362-11-100C	1 × 1	100	Ceramic	0	0			0	
S12652-050C	S10362-33-050C	3 × 3	50	Ceramic	0	0			0	
S12652-100C	S10362-33-100C	3 × 3	100		0	0			0	
S12671-050	S11028-050	1 × 1	50		0	0			0	0
S12671-100	S11028-100		100	Metal	0	0			0	0
S12672-050	-	3 × 3	50	(Two-stage TE-cooled)	0	0			0	0
S12672-100	-	3 × 3	100		0	0			0	0

#### Buttable type (semi-custom made) Preliminary

These MPPCs employ a structure that reduced insensitive portions formed along the periphery of the photosensitive area. The 4-side buttable structure allows them to be arrayed in two dimensions at equal intervals.

Type. no	Previous product	Photosensitive area per 1 ch (mm)	Pixel pitch (µm)	Package	Low dark count	Low afterpulse	High photon detection efficiency	Low crosstalk	3-side buttable	4-side buttable
S12641-050	S10931-050P	3 × 3		TSV,	0	0	0			0
S12642-050	S11064-050P	$3 \times 3$ (4 × 4 ch array)	50	Surface mount type	0	0	0			0

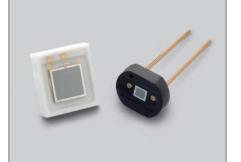
# Carge area arrays Preliminary

These are monolithic arrays comprised of multiple 3 × 3 mm MPPCs formed on a single chip.

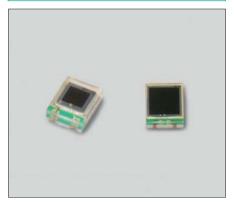
Type. no	Previous product	Photosensitive area per 1 ch (mm)	Pixel pitch (µm)	Package	Low dark count	Low afterpulse	High photon detection efficiency	Low crosstalk	3-side buttable	4-side buttable
S12657-050	S11827-3344MG			Wire bonding, PWB	0	0	0			
S12658-050	S11828-3344M	3 × 3	50	Wire bonding, surface mount type	0	0	0		0	
S12659-050	S11829-3344MF	(4 × 4 ch array)	4 ch array)	Wire bonding,	0	0	0		0	
S12660-050	S11830-3344MF			surface mount type with FPC	0	0	0		0	
S12573-025C	S10985-025C		25		0	0	0			
S12573-050C	S10985-050C	$3 \times 3$ (2 × 2 ch array)	3 × 3 × 2 ch array) 50 100	Ceramic	0	0	0			
S12573-100C	S10985-100C				0	0	0			

#### MPPC packages

#### Ceramic



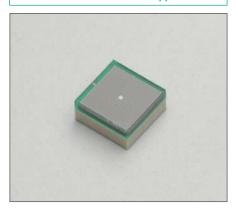
Surface mount type



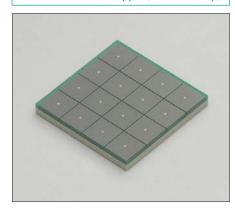
Metal (TE-cooled)



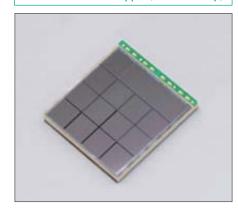
4-side buttable type



4-side buttable type (16 ch array)



3-side buttable type (16 ch array)



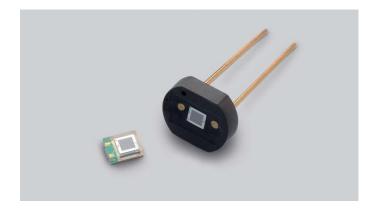
# MPPC for general measurement



# S12571-025, -050, -100C/P

The S12571 series are general-purpose MPPC with drastically reduced afterpulses compared to our previously marketed products. By widening the operating voltage range and improving the time resolution and photon detection efficiency, the S12571 series offer the characteristics needed for a variety of applications. These MPPCs have a photosensitive area of 1  $\times$  1 mm and are available in a ceramic package or surface mount type.

· MPPC modules: C11205-150/-350 (analog output type)



The following characteristics were measured at the operating voltage that yields the listed gain. (See the data attached to each product.)

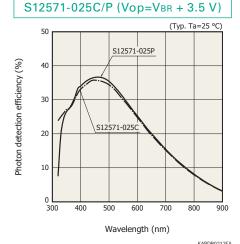
(Typ. Ta=25 °C, unless otherwise noted)

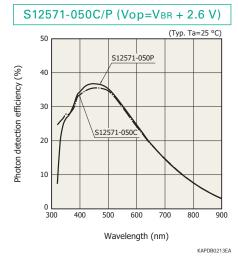
D		Courselle and		S12571		1.1		
Paramet	er	Symbol	-025C, -025P	-050C, -050P	-100C, -100P	Unit		
Effective photosens	itive area	-	1 x 1					
Pixel pitch		-	25	50	100	μm		
Number of pixels		-	1600 400 100		-			
Spectral response r	ange	λ		nm				
Peak sensitivity way	elength	λр		nm				
Photon detection effic	iency (λ=λp)*1	PDE		%				
Breakdown voltage		VBR	65 ± 10					
Operating voltage		Vop	VBR + 3.5	VBR + 2.6	VBR + 1.4	V		
Dark count*2	Тур.			100		liana		
Dark count -	Max.	- [		200		kcps		
Terminal capacitano	е	Ct		35		pF		
Time resolution (FV	/HM)* <sup>3</sup>	-	250	250	300	ps		
Temperature coeffice operating voltage	ient of	-		mV/°C				
Gain		М	$5.15 \times 10^{5}$	$1.25 \times 10^{6}$	2.8 × 10 <sup>6</sup>	-		
Temperature coeffic	ient of gain	-	8.2 × 10 <sup>3</sup>	2.7 × 10 <sup>4</sup>	1.2 × 10 <sup>5</sup>	/°C		

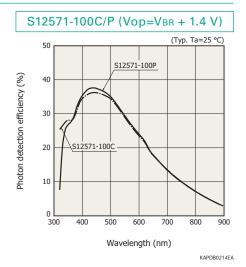
<sup>\*1:</sup> Photon detection efficiency does not include crosstalk and afterpulses.

Note: The last letter of each type number indicates the package type (C: ceramic, P: surface mount type).

#### Photon detection efficiency vs. wavelength







Photon detection efficiency does not include crosstalk and afterpulses.

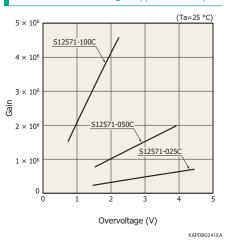
<sup>\*2:</sup> Threshold=0.5 p.e.

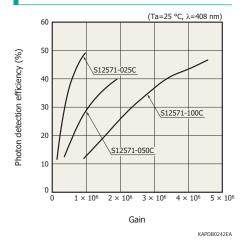
<sup>\*3:</sup> Single photon level

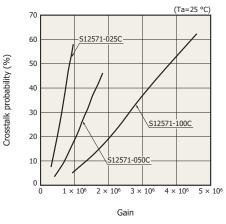
#### Gain vs. overvoltage (typical example)

#### Photon detection efficiency vs. gain (typical example)

#### Crosstalk probability vs. gain (typical example)



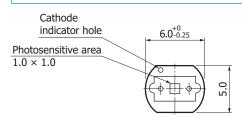


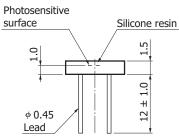


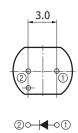
MPPC characteristics vary with the operating voltage. The 25  $\mu$ m pixel pitch type is suitable for applications requiring a wide dynamic range, because it has a large number of pixels and provides narrow-width output pulses. The 100  $\mu$ m pixel pitch type is suitable for applications where high gain is essential. Although increasing the operating voltage improves the photon detection efficiency and time resolution, it also increases the dark count and crosstalk at the same time, so an optimum operating voltage must be selected to match the application.

#### Dimensional outlines (unit: mm)

#### S12571-025C/-050C/-100C



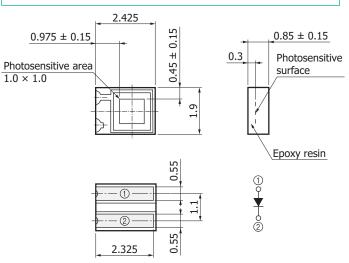




Tolerance unless otherwise noted: ±0.2

KAPDA0141EA

#### S12571-025P/-050P/-100P



Tolerance unless otherwise noted: ±0.1

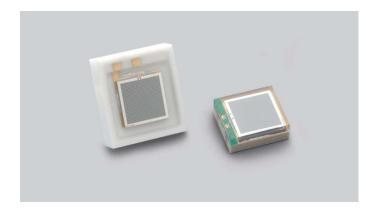
KAPDA0142EA



# S12572-025, -050, -100C/P

The S12572 series are general-purpose MPPC with drastically reduced afterpulses compared to our previously marketed products. By widening the operating voltage range and improving the time resolution and photon detection efficiency, the S12572 series offer the characteristics needed for a variety of applications. These MPPCs have a photosensitive area of  $3\times3$  mm and are available in a ceramic package or surface mount type.

· MPPC modules: C11205-150/-350 (analog output type)



The following characteristics were measured at the operating voltage that yields the listed gain. (See the data attached to each product.)

(Typ. Ta=25 °C, unless otherwise noted)

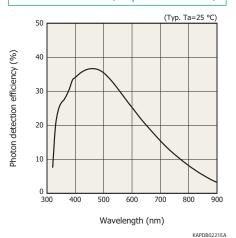
Des		Consolnat		S12572		I I and the		
Parame	ter	Symbol	-025C, -025P	-050C, -050P	-100C, -100P	Unit		
Effective photosen	sitive area	-	3 × 3					
Pixel pitch		-	25	50	100	μm		
Number of pixels		-	14400	-				
Spectral response	range	λ		nm				
Peak sensitivity wa	velength	λр		nm				
Photon detection effi	ciency (λ=λp)*1	PDE		%				
Breakdown voltage		VBR		65 ± 10		V		
Operating voltage		Vop	VBR + 3.5	VBR + 2.6	VBR + 1.4	V		
D 1 1+2	Тур.			1000				
Dark count*2	Max.	-		2000		kcps		
Terminal capacitan	ce	Ct		320		pF		
Time resolution (FV	VHM)*3	-	300 300 400					
Temperature coefficient of operating voltage -		-		60	1	mV/°C		
Gain		М	$5.15 \times 10^5$ $1.25 \times 10^6$ $2.8 \times 10^6$			-		
Temperature coefficient of gain -		8.2 × 10 <sup>3</sup>	2.7 × 10 <sup>4</sup>	1.2 × 10 <sup>5</sup>	/°C			

<sup>\*1:</sup> Photon detection efficiency does not include crosstalk and afterpulses.

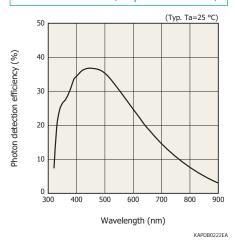
Note: The last letter of each type number indicates the package type (C: ceramic, P: surface mount type).

#### Photon detection efficiency vs. wavelength

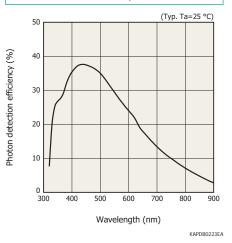
#### S12572-025C/P (Vop=VBR + 3.5 V)



#### S12572-050C/P (Vop=VBR + 2.6 V)



#### S12572-100C/P (Vop=VBR + 1.4 V)



Photon detection efficiency does not include crosstalk and afterpulses.

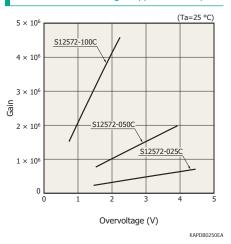
<sup>\*2:</sup> Threshold=0.5 p.e.

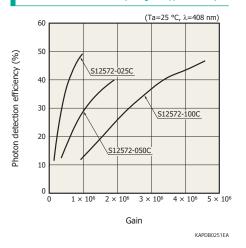
<sup>\*3:</sup> Single photon level

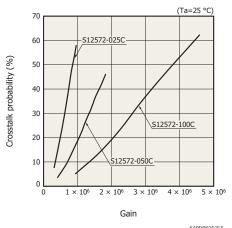
#### Gain vs. overvoltage (typical example)

#### Photon detection efficiency vs. gain (typical example)

#### Crosstalk probability vs. gain (typical example)



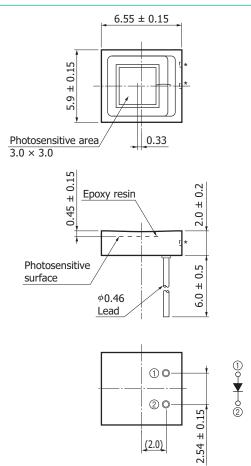




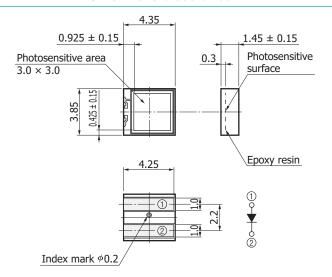
MPPC characteristics vary with the operating voltage. The 25 µm pixel pitch type is suitable for applications requiring a wide dynamic range, because it has a large number of pixels and provides narrow-width output pulses. The 100 μm pixel pitch type is suitable for applications where high gain is essential. Although increasing the operating voltage improves the photon detection efficiency and time resolution, it also increases the dark count and crosstalk at the same time, so an optimum operating voltage must be selected to match the application.

#### Dimensional outlines (unit: mm)

#### S12572-025C/-050C/-100C



#### S12572-025P/-050P/-100P



Tolerance unless otherwise noted: ±0.1

KAPDA0144EA

Tolerance unless otherwise noted: ±0.2

\* Metal electrodes connecting to the internal electrodes are exposed on the sides of the ceramic package. To avoid short circuits, never allow other conductors to come in contact with these metal electrodes.

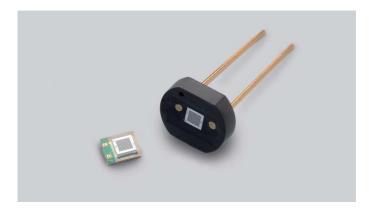
KAPDA0143FB

# High-speed, wide dynamic range MPPC



# S12571-010, -015C/P

These MPPCs utilize very small pixels arrayed at high densities to achieve a highspeed recovery time and wide dynamic range. Hamamatsu currently produces MPPC with a pixel density up to 10000 pixels/mm $^2$  (pixel pitch: 10  $\mu$ m). Utilizing advanced technology to enhance photon detection efficiency minimizes the drop in photon detection efficiency that usually occurs due to shrinking the pixel pitch. · MPPC module: C11209-110 (analog output type)



The following characteristics were measured at the operating voltage that yields the listed gain. (See the data attached to each product.) (Typ. Ta=25 °C, unless otherwise noted)

ъ.		0 1 1	S12	2571	
Paramet	er	Symbol	-010C, -010P	-015C, -015P	Unit
Effective photosens	tive area	-	1	× 1	mm
Pixel pitch		-	10	15	μm
Number of pixels		-	10000	4489	-
Spectral response ra	inge	λ	320 1	to 900	nm
Peak sensitivity way	elength	λρ	470	460	nm
Photon detection effic	iency (λ=λp)*1	PDE	10	25	%
Breakdown voltage		VBR	65	± 10	V
Operating voltage		Vop	VBR + 4.5	VBR + 4.0	V
D 1 +2	Тур.		1	00	
Dark count*2	Max.	-	2	00	kcps
Terminal capacitanc	9	Ct	3	35	pF
Time resolution (FW	'HM)* <sup>3</sup>	-	300	250	ps
Temperature coefficient of	operating voltage	-	(	60	mV/°C
Gain		М	1.35 × 10 <sup>5</sup>	2.3 × 10 <sup>5</sup>	-
Temperature coeffic	ient of gain	-	1.6 × 10 <sup>3</sup>	3.5 × 10 <sup>3</sup>	/°C

<sup>\*1:</sup> Photon detection efficiency does not include crosstalk and afterpulses.

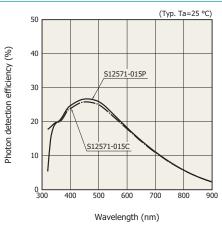
Note: The last letter of each type number indicates the package type (C: ceramic, P: surface mount type).

#### Photon detection efficiency vs. wavelength

#### S12571-010C/P (Vop=VBR + 4.5 V)

# (Typ. Ta=25 °C) 50 Photon detection efficiency (%) 30 20 S12571-010F 10 400 600 Wavelength (nm)

#### S12571-015C/P (Vop=VBR + 4.0 V)



KAPDB0216EA

Photon detection efficiency does not include crosstalk and afterpulses.

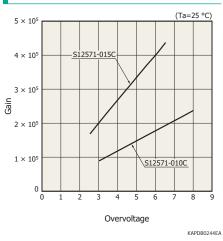
<sup>\*2:</sup> Threshold=0.5 p.e.

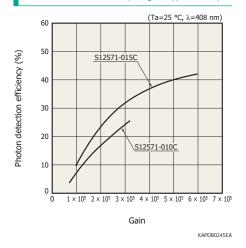
<sup>\*3:</sup> Single photon level

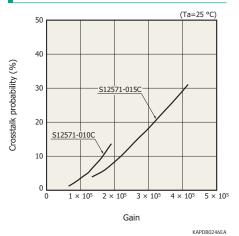


#### Photon detection efficiency vs. gain (typical example)

#### Crosstalk probability vs. gain (typical example)



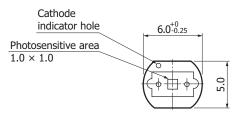


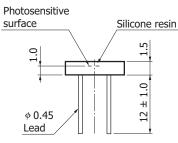


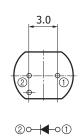
Because the high-speed, wide dynamic range MPPC has a small pixel capacitance, the gain is smaller than the MPPC for general measurement. The gain and photon detection efficiency are increased by applying the higher operating voltage. Please use it with the appropriate operating voltage because the crosstalk increases at the same time.

#### Dimensional outlines (unit: mm)

#### S12571-010C/-015C

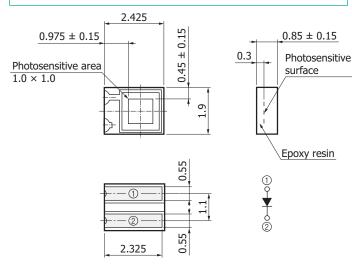






Tolerance unless otherwise noted:  $\pm 0.2$ 

#### S12571-010P/-015P





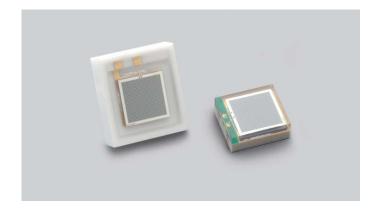
KAPDA0142EA

KAPDA0141EA

# S12572-010, -015C/P

These MPPCs utilize very small pixels arrayed at high densities to achieve a highspeed recovery time and wide dynamic range. Hamamatsu currently produces MPPC with a pixel density up to 10000 pixels/mm<sup>2</sup> (pixel pitch: 10 µm). Utilizing advanced technology to enhance photon detection efficiency minimizes the drop in photon detection efficiency that usually occurs due to shrinking the pixel pitch.

· MPPC module: C11209-110 (analog output type)



The following characteristics were measured at the operating voltage that yields the listed gain. (See the data attached to each product.) (Typ. Ta=25 °C, unless otherwise noted)

-		0 1 1	S1	2572	11.2
Parameter		Symbol	-010C, -010P	-015C, -015P	Unit
Effective photosensitive area		-	3 × 3		mm
Pixel pitch		-	10	15	μm
Number of pixels		-	90000	40000	-
Spectral response	range	λ	320	to 900	nm
Peak sensitivity wavelength		λр	470	460	nm
Photon detection efficiency $(\lambda = \lambda p)^{*1}$		PDE	10 25		%
Breakdown voltage		VBR	65 ± 10		V
Operating voltage		Vop	VBR + 4.5 VBR + 4.0		V
Dark count*2	Тур.		1000 2000		kcps
Dark count"	Max.	-			
Terminal capacitan	ce	Ct	3	320	pF
Time resolution (FWHM)*3		-	500	400	ps
Temperature coefficient of operating voltage		-	60		mV/°C
Gain		М	1.35 × 10 <sup>5</sup>	2.3 × 10 <sup>5</sup>	-
Temperature coefficient of gain		-	$1.6 \times 10^3$ $3.5 \times 10^3$		/°C

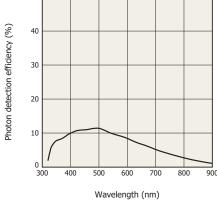
<sup>\*1:</sup> Photon detection efficiency does not include crosstalk and afterpulses.

Note: The last letter of each type number indicates the package type (C: ceramic, P: surface mount type).

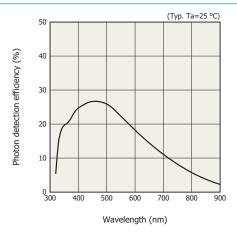
#### Photon detection efficiency vs. wavelength

#### (Typ. Ta=25 °C) 50 40

S12572-010C/P (Vop=VBR + 4.5 V)



#### S12572-015C/P (Vop=VBR + 4.0 V)



Photon detection efficiency does not include crosstalk and afterpulses.

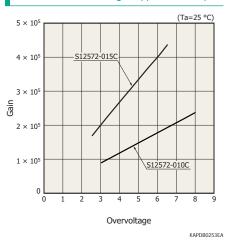
<sup>\*2:</sup> Threshold=0.5 p.e.

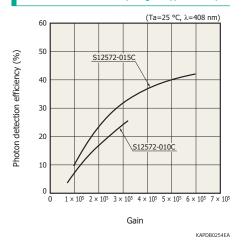
<sup>\*3:</sup> Single photon level

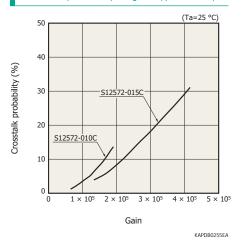
#### Gain vs. overvoltage (typical example)

#### Photon detection efficiency vs. gain (typical example)

#### Crosstalk probability vs. gain (typical example)





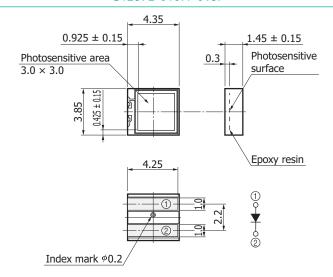


Because the high-speed, and wide dynamic range MPPC has a small pixel capacitance, the gain is smaller than the MPPC for general measurement. The gain and photon detection efficiency are increased by applying the higher operating voltage. Please use it with the appropriate operating voltage because the crosstalk increases at the same time.

#### Dimensional outlines (unit: mm)

# S12572-010C/-015C $6.55 \pm 0.15$ $5.9 \pm 0.15$ Photosensitive area 0.33 $3.0 \times 3.0$ $0.45 \pm 0.15$ 0.2 Epoxy resin $2.0 \pm ($ Photosensitive surface $6.0 \pm 0.9$ $\phi$ 0.46 Lead 100 20 $54 \pm 0.15$

#### S12572-010P/-015P



Tolerance unless otherwise noted: ±0.1

KAPDA0144EA

Tolerance unless otherwise noted: ±0.2

\* Metal electrodes connecting to the internal electrodes are exposed on the sides of the ceramic package. To avoid short circuits, never allow other conductors to come in contact with these metal electrodes.

(2.0)

KAPDA0143FB

# MPPC for very low light level measurement



# \$12576-050, \$12577-050

The S12576-050 and S12577-050 are MPPC devices that contain a thermoelectric cooler to avoid the drop in S/N caused by the dark count. The dark count decreases by half for every approx. 8 °C drop in element temperature.

· MPPC modules

C11208-150/-350 (analog/digital output type)

C12661-150/-350 (digital output type)

C12662-150/-350 (analog output type)



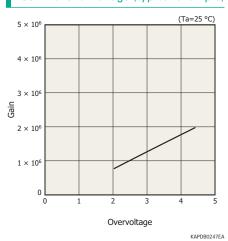
The following characteristics were measured at the operating voltage that yields the listed gain. (See the data attached to each product.)

(Typ. Td=-10 °C)

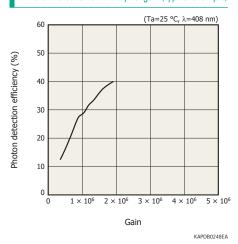
					(1)p. 14- 10 C
Parame	ter	Symbol	S12576-050	S12577-050	Unit
Effective photosens	sitive area	-	1 × 1		mm
Pixel pitch		-		μm	
Number of pixels		-	400 3600		-
Spectral response	ange	λ	320	to 900	nm
Peak sensitivity wa	velength	λρ	4	150	nm
Photon detection efficiency $(\lambda = \lambda p)^{*1}$		PDE	:	%	
Breakdown voltage		VBR	62.9	V	
Operating voltage		Vop	VBR	V	
D 1 1+2	Тур.		5 50		
Dark count*2	Max.	-	10	100	kcps
Terminal capacitano	e	Ct	35	320	pF
Time resolution (FV	VHM)*3	-	250	250	ps
Temperature coefficient of operating voltage		-	60		mV/°C
Gain		M	1.25	-	
Temperature coeffic	cient of gain	-	2.7	/°C	

<sup>\*1:</sup> Photon detection efficiency does not include crosstalk and afterpulses.

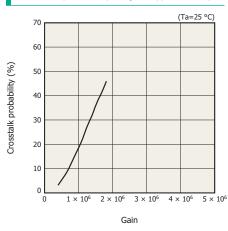
#### Gain vs. overvoltage (typical example)



#### Photon detection efficiency vs. gain (typical example)



#### Crosstalk probability vs. gain (typical example)



KAPDB0249EA

<sup>\*2:</sup> Threshold=0.5 p.e.

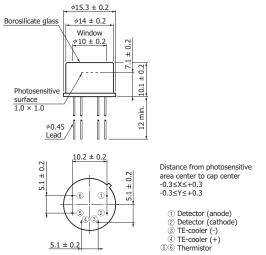
<sup>\*3:</sup> Single photon level

#### Photon detection efficiency vs. wavelength

# (Typ. Ta=25 °C, Vop=V<sub>BR</sub> + 2.6 V) Photon detection efficiency (%) 40 30 20 10 400 800 Wavelength (nm) KAPDB0220EA

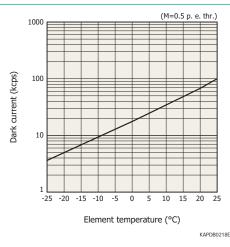
Photon detection efficiency does not include crosstalk and afterpulses.

#### Dimensional outline (unit: mm)

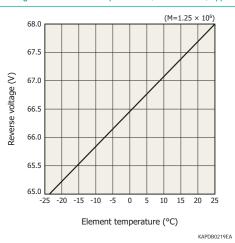


KAPDA0145EA

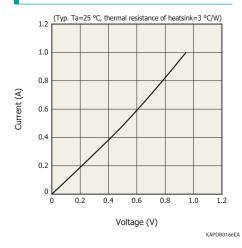
#### Dark current vs. element temperature (S12576-050, typical example)



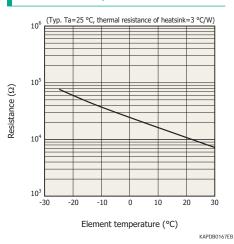
#### Reverse voltage vs. element temperature (\$12576-050, typical example)



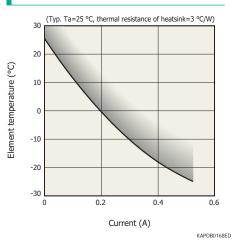
#### Current vs. voltage of TE-cooler



#### Thermistor temperature characteristics



#### Cooling characteristics of TE-cooler



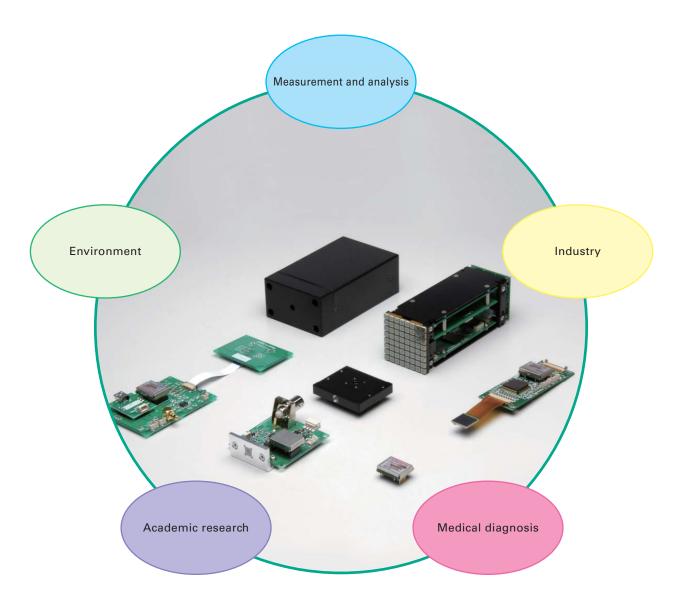
In this data, MPPC is not operated. When MPPC is in operation, the data will vary because the amount of heat generated in MPPC changes depending on the applied reverse voltage and incident light level.

# MPPC modules

#### ▶ Optical measurement modules capable of measuring very low light levels

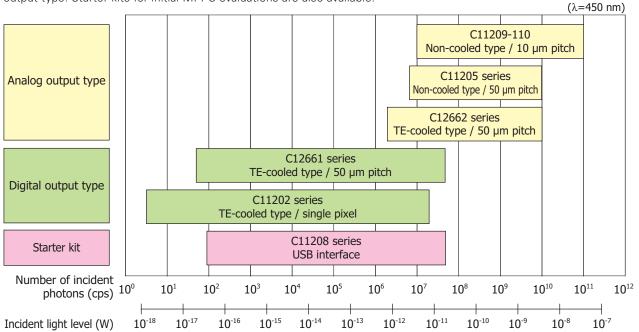
Hamamatsu MPPC modules are optical measurement modules capable of measuring light over a wide range of light levels (10 orders of magnitude) from the photon-counting region up to the nW (nano watt) region. MPPC modules contain a signal amplifier circuit, a high-voltage power supply circuit, and other components needed for MPPC operation. MPPC modules operate just by connecting them to a power supply (±5 V, etc).

Hamamatsu offers a wide lineup of MPPC modules including cooled modules that give a low dark count and non-cooled modules with a temperature compensation function for stable measurement. Hamamatsu also provides starter kits developed for making initial MPPC evaluations and a temperature-compensated high-voltage power supply module designed to operate an MPPC. Besides standard product modules, we also welcome your requests for custom-made designs.

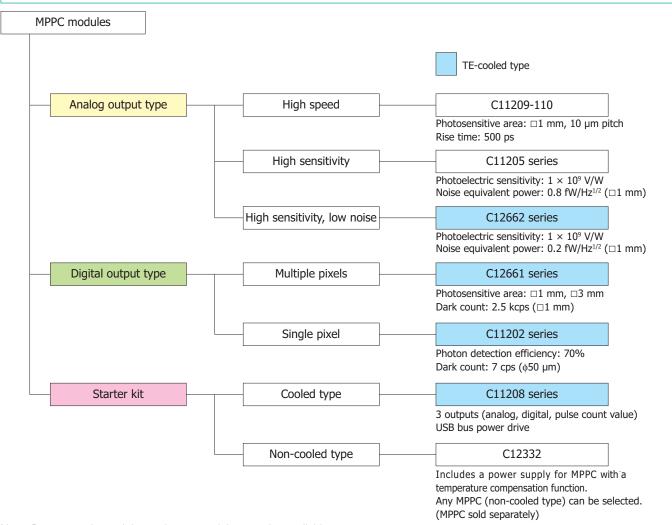


#### ► Measurable light level range

MPPC modules include two output types according to the incident light level (number of photons): analog output type and digital output type. Starter kits for initial MPPC evaluations are also available.



#### ▶ Broad product lineup to meet diverse applications



Note: Power supply modules and array modules are also available.

#### ▶ Selecting the digital output type or analog output type

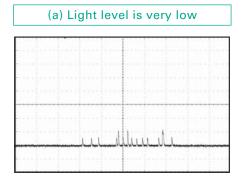
The output type (digital or analog) should be selected according to the light level incident on the MPPC module.

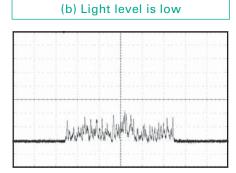
The following output waveforms (a) (b) and (c) show MPPC output waveforms measured at different incident light levels and observed on an oscilloscope. The incident light level was increased in the order of (a) (b) and (c), starting from (a) at very low light levels. The output signal of (a) as seen here consists of discrete pulses. In this state, selecting the digital output type allows measuring at a higher S/N, where the signals are binarized and the number of pulses is digitally counted. Since the digital output type can easily subtract the dark count from the signal, the detection limit is determined by dark count fluctuations.

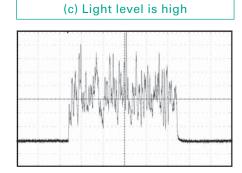
As the light level increases, the output waveform consists of pulses overlapping each other [Output waveforms (b) (c)]. In this state, the number of pulses cannot be counted and the analog output type should be selected to measure the analog output and find the average value. The detection limit in the analog output type is determined by the dark current shot noise and the cutoff frequency of the readout circuit.

The bottom graphs show dynamic range of analog output type (C12662-350) and digital output type (C12661-350).

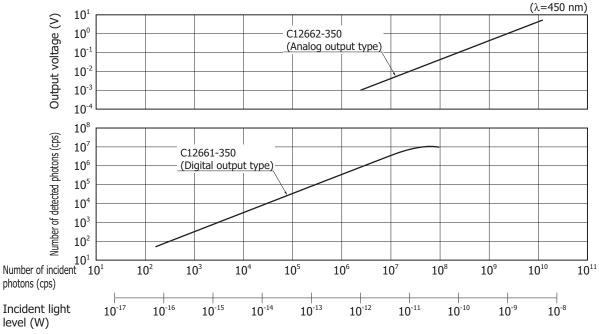
#### Output waveforms





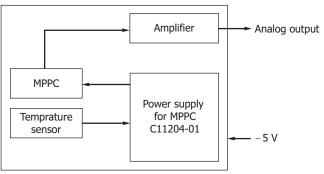


#### Dynamic range



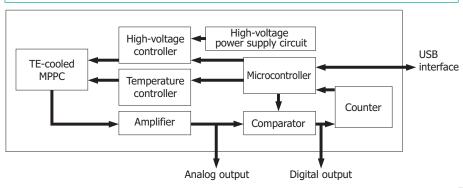
KACCB0311EA

#### Analog output type (C11205 series)



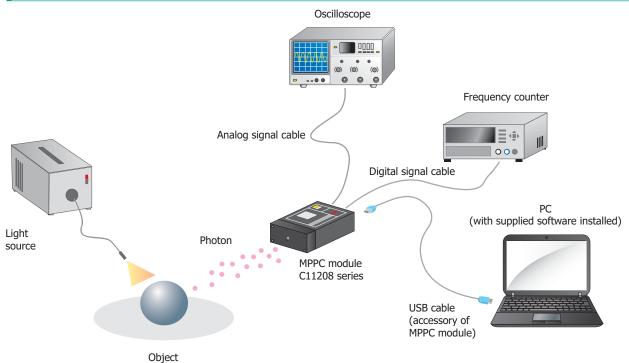
KACCC0675EA

#### Digital output type (C11208 series)



KACCC0518EA

#### Connection example



KACCC0516EB

# MPPC module lineup

# Analog output type NEW

Type no.	Photo W x D x H (mm)	Photosensitive area	Pixel pitch	Internal MPPC	Noise equivalent power	High-band cutoff frequency	Temperature control	Supply voltage	Features	
C11209-110	45 × 38 × 13	□ 1 mm	10 µm	S12571-010C	3 fW/Hz <sup>1/2</sup>	40 MHz (rise time: 500 ps)	Temperature compensation (non-cooled)	+5 V	High speed     Compact size	
C11205-150	No.	□1 mm	E0 um	S12571-050C	0.8 fW/Hz <sup>1/2</sup>	7 MHz	Temperature compensation (non-cooled)	±5 V	• High sensitivity (1 × 10 <sup>9</sup> V/W)	
C11205-350	50 × 50 × 19.6		50 μm S12572-0	S12572-050C	2 fW/Hz <sup>1/2</sup>				High sensitivity (1 x 10° v/vv)	
C12662-150		□ 1 mm		FO	S12576-050	0.2 fW/Hz <sup>1/2</sup>	7 1 1 1 -	TE-cooled	5.4	• High sensitivity (1 × 10 <sup>9</sup> V/W)
C12662-350	12662-350 98 × 60 × 35	□ 3 mm	50 μm	S12577-050	0.4 fW/Hz <sup>1/2</sup>	7 MHz	(-20 °C)	±5 V	Low noise	

# Digital output type NEW

Type no.	Photo W x D x H (mm)	Photosensitive area	Pixel pitch	Internal MPPC	Dark count	Maximum count rate	Temperature control	Supply voltage	Features
C12661-150		□1 mm	50 μm	S12576-050	2.5 kcps	10 Mcps	TE-cooled (-20 °C)	±5 V	High photon detection efficiency (35%)  Low dark count  Low afterpulse
C12661-350	98 × 60 × 35	□ 3 mm		S12577-050	25 kcps				
C11202-050		φ50 μm	-	Single pixel type	7 cps	30 Mcps	TE-cooled	±5 V	High photon detection efficiency (70%)
C11202-100	98 × 60 × 35	φ100 μm	-	30 cps	20 Mcps	(-20 °C)	±3 V	<ul><li>Low dark count</li><li>Low afterpulse</li></ul>	

# Starter kits NEW

Type no.	Photo W x D x H (mm)	Photosensitive area	Pixel pitch	Internal MPPC	Temperature control	Supply voltage	Features	
C11208-150		□1 mm	E0.4100	S12576-050	TE-cooled (-10 °C)	USB bus power	Suitable for initial MPPC evaluations; supports 3 outputs (analog, digital, and pulse count value)	
C11208-350	98 × 60 × 35	□ 3 mm	—— 50 μm nm	S12577-050	TE-cooled (0 °C)		USB bus power drive	
C12332	70 × 50 × 11.4	Evaluat	tes any non (sold sepa	-cooled MPPC rately)	Temperature compensation (non-cooled)	±5 V	Simple initial MPPC evaluations     Includes C11204-01 power supply for MPPC     Measurable just by setting MPPC operating voltage from PC	

# Power supply module NEW

Type no.	Photo W x D x H (mm)	Input voltage range	Output voltage range	Ripple noise typ.*1	Temperature stability typ.	Setting resolution	Features
C11204-01	19.4 × 17 × 6.3	5 V	50 to 90 V	0.1 mVp-p	±10 ppm/°C	1.8 mV	Includes high-precision temperature compensation function (temperature stability: ±10 ppm/°C typ.)     Various settings possible via serial interface

<sup>\*1:</sup> No load; recommended circuit is used

# Array modules

Array modules are available in various types. Contact us for detailed information.



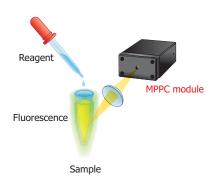




# **Application examples of MPPC modules**

Application examples of Hamamatsu MPPC modules are shown below.

#### Fluorescence measurement

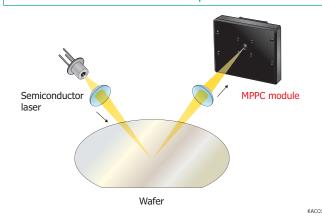


KACCC0664EA

KACCC0598EA

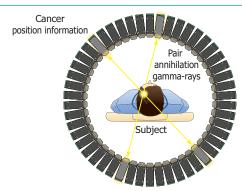
Major characteristics High photon detection efficiency, low afterpulse Suitable MPPC modules C12661 series, C12662 series

#### Disc surface inspection



Major characteristics High-speed response, wide dynamic range Suitable MPPC modules C11209 series

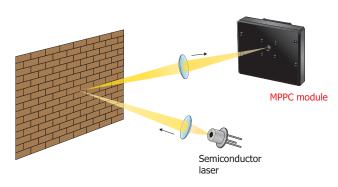
#### Scintillation measurement



MPPC module (array type)

Major characteristics Wide dynamic range Suitable MPPC modules C11205 series

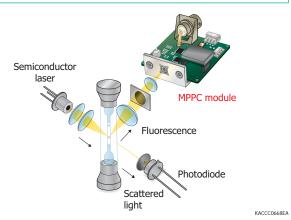
#### Distance measurement



KACCC0666EA

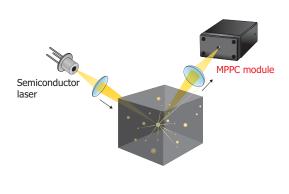
Major characteristics High-speed response, wide dynamic range Suitable MPPC modules C11209 series

#### Flow cytometry



Major characteristics High photon detection efficiency Suitable MPPC modules C11205 series, C12662 series

#### Particle measurement



KACCC0667EA

Major characteristics High photon detection efficiency, low afterpulse Suitable MPPC modules C11202 series

# **Analog output type MPPC modules**



# C11209-110

The C11209-110 is an optical measurement module capable of detecting low level light. It consists of an MPPC, a high-speed amplifier circuit, a high-voltage circuit, and a temperature compensation circuit. Utilizing a small pixel pitch (10 µm) MPPC allows high-speed measurement over a wide dynamic range, making the C11209-110 suitable for high-speed signal measurement such as distance measurement. The C11209-110 operate just by connecting it to an external single power supply (+5 V).

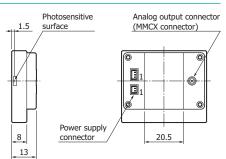


(Typ. Ta=25 °C,  $\lambda = \lambda p$ , Vs=+5 V, unless otherwise noted)

Para	meter	Symbol	C11209-110	Unit
Internal MPPC		-	S12571-010C	-
Effective photos	ensitive area	-	1 x 1	mm
Pixel pitch		-	10	μm
Number of pixel	S	-	10000	-
Spectral respons	se range	λ	320 to 900	nm
Peak sensitivity wavelength		λр	520	nm
Temperature stability of output voltage		-	±5 max.	%
Photoelectric se	ensitivity	-	2.6 × 10 <sup>6</sup>	V/W
Rise time		tr	500	ps
2	High band		40	MHz
Cutoff frequency	Low band	fc	10	kHz
Noise equivalent power		NEP	3	fW/Hz <sup>1/2</sup>
Minimum detection limit		-	20	pW rms
Saturation input light level		-	100	nW
Dimensions		- 45 × 38 × 13		mm

#### Dimensional outline (unit: mm)

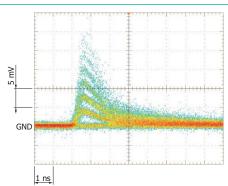
# Photosensitive area (4 x) M2.6 depth 4 R 0 0 0 0 40 ± 0.3 45 ± 0.3 M6 depth 5



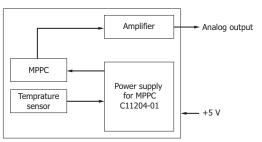
Tolerance unless otherwise noted: ±0.2

#### KACCA0312EA

#### Analog output waveforms



#### Block diagram



KACCC0675EA



#### C11205 series

The C11205 series are optical measurement modules capable of detecting low level light. These modules consist of an MPPC, a signal amplifier circuit, a high-voltage power supply circuit, and a temperature compensation circuit. The photosensitive area is available in two sizes of 1  $\times$  1 mm and 3  $\times$  3 mm, and the signal output is analog. Modules operate just by connecting them to an external power supply (±5 V).

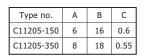


(Typ. Ta=25 °C,  $\lambda=\lambda p$ , Vs=±5 V, unless otherwise noted)

Para	Parameter Symb		C11205-150	C11205-350	Unit
Internal MPPC		-	S12571-050C S12572-050C		-
Effective photos	sensitive area	-	1 × 1 3 × 3		mm
Pixel pitch		-	5	50	μm
Number of pixe	ls	-	400	3600	-
Spectral response range		λ	320 t	to 900	nm
Peak sensitivity wavelength		λр	500		
Temperature stability of output voltage -		-	±5।	%	
Photoelectric se	ensitivity	-	1.0 :	V/W	
0.4-44.6	High band	f -		7	MHz
Cutoff frequency	Low band	fc	DC		-
Noise equivalen	t power	NEP	0.8	2	fW/Hz <sup>1/2</sup>
Minimum detection limit -		-	2.5 5.5		pW rms
Maximum output voltage -		-	4.9		V
Dimensions -		-	50 × 50	mm	

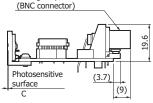
#### Dimensional outline (unit: mm)

# Power supply connector 20 45 (4 ×) ø 3.2 9 50 Analog output connector (BNC connector) Photosensitive area



25

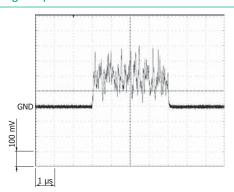
35

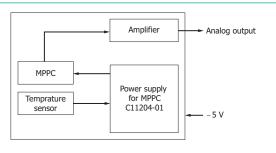


Tolerance unless otherwise noted: ±0.3

KACCA0310EA

#### Analog output waveform







#### C12662 series

The C12662 series are optical measurement modules capable of detecting low light levels. These modules consist of a thermoelectrically cooled MPPC, a signal amplifier circuit, a high-voltage power supply circuit, and a temperature control circuit. The photosensitive area is available in two sizes of  $1 \times 1$  mm and  $3 \times 3$  mm, and the signal output is analog. Modules operate just by connecting them to an external power supply (±5 V).

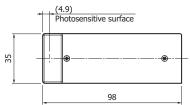


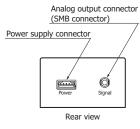
(Typ. Ta=25 °C,  $\lambda=\lambda p$ , Vs=±5 V, unless otherwise noted)

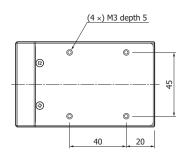
Parai	meter	Symbol	C12662-150	C12662-350	Unit				
Internal MPPC		-	S12576-050 S12577-050		-				
Effective photosensitive area		-	1 × 1 3 × 3		mm				
Pixel pitch		-	5	50	μm				
Number of pixel	s	-	400	3600	-				
Spectral respons	se range	λ	320 t	o 900	nm				
Peak sensitivity wavelength		λр	500						
Element temperature (setting temperature)		Td	-20						
Photoelectric se	nsitivity	-	1.0 × 10 <sup>9</sup>						
Cutoff from consu	High band	40	7 DC		MHz				
Cutoff frequency	Low band	fc			-				
Noise equivalen	t power	NEP	0.2	0.4	fW/Hz <sup>1/2</sup>				
Minimum detection limit		-	0.55 1.1		pW rms				
Maximum output voltage		-	4.9		V				
Dimensions -		-	98 × 60 × 35		mm				

#### Dimensional outline (unit: mm)

# Photosensitive area 0 0 0 60

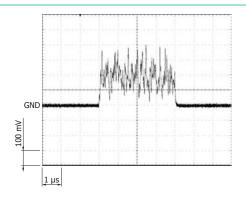


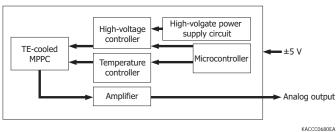




Tolerance unless otherwise noted:  $\pm 0.5$ KACCA0314EA

#### Analog output waveform





# Digital output type MPPC modules



# C12661 series

The C12661 series are photon counting modules capable of detecting low light levels. These modules consist of a thermoelectrically cooled MPPC, a signal amplifier circuit, a comparator circuit, a high-voltage power supply circuit, and a temperature control circuit. The photosensitive area is available in two sizes of  $1 \times 1$  mm and  $3 \times 3$  mm, and the signal output is digital. Modules operate just by connecting them to an external power supply (±5 V).



(Typ. Ta=25 °C,  $\lambda=\lambda p$ , Vs=±5 V, unless otherwise noted)

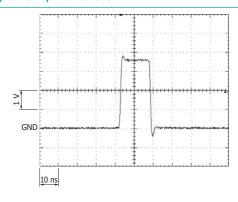
Parameter	Symbol	C12661-150	C12661-350	Unit
Internal MPPC	-	S12576-050	S12577-050	-
Effective photosensitive area	-	1 × 1	3 × 3	mm
Pixel pitch	-	5	50	μm
Number of pixels	-	400	3600	-
Spectral response range	λ	320 t	to 900	nm
Peak sensitivity wavelength	λр	4!	nm	
Element temperature (setting temperature)	Td	-2	°C	
Photon detection efficiency*	PDE	3	35	%
Dark count*	-	2.5	25	kcps
Afterpulse probability	-		1	%
Comparator output	-	TTL cor	mpatible	-
Comparator threshold level	-	Can be set in 10 steps fro	p.e.	
Maximum count rate	-	1	Mcps	
Dimensions	-	98 × 6	60 × 35	mm

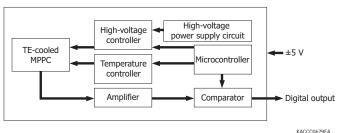
<sup>\*0.5</sup> p.e. (threshold level)

#### Dimensional outline (unit: mm)

#### (4.9) Photosensitive surface Photosensitive area 0 0 0 0 98 Rotary switch (comparator threshold level) Power supply connector (4 x) M3 depth 5 (3) Digital output connector **③** (SMB connector) Back view Tolerance unless otherwise noted: ±0.5

#### Digital output waveform







#### C11202 series

The C11202 series is a single-photon counting module capable of detecting low light levels. The C11202 series is made up of a single-pixel thermoelectrically cooled MPPC, a signal amplifier circuit, a comparator circuit, a high-voltage power supply circuit, and a temperature control circuit. The photosensitive area is available in two sizes of  $\phi 50~\mu m$  and  $\phi 100~\mu m$ , and such small photosensitive areas offer a low dark count. Modules operate just by connecting them to an external power supply (±5 V).

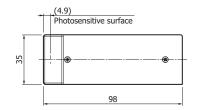


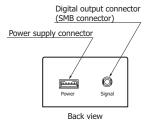
(Typ. Ta=25 °C,  $\lambda=\lambda p$ , Vs= $\pm 5$  V, unless otherwise noted)

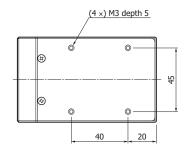
Pa	rameter	Symbol	C11202-050	C11202-100	Unit	
Internal MPPC		-	Single pixel type		-	
Effective photosensitive area		-	φ50	φ100	μm	
Number of pix	els	-		1	-	
Spectral respo	nse range	λ	320 t	0 900	nm	
Peak sensitivity wavelength		λр	450			
Element temperature (setting temperature)		Td	-20			
Photon detect	ion efficiency	PDE	70			
Dark count		-	7 30		cps	
Afterpulse	to 100 ns		1	1.5	%	
probability	from 100 ns	-	0.01			
Comparator output		-	TTL cor	mpatible	-	
Maximum count rate		-	30	20	Mcps	
Dimensions -		-	98 × 60 × 35			

#### Dimensional outline (unit: mm)

#### Photosensitive area 0 0 0 0 60

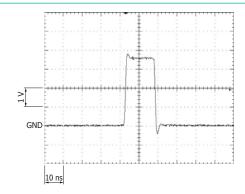


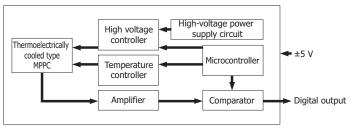




Tolerance unless otherwise noted: ±0.5

#### Digital output waveform





# Starter kits



# C11208 series

The C11208 series are starter kits designed for evaluating thermoelectrically cooled MPPC. These starter kits have a USB interface that allows you to change the threshold level and acquire data from a PC. No external power supply is needed since they operate on USB bus power. Three signal output formats of analog, digital, and pulse count (USB) are provided.



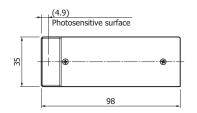
(Typ. Ta=25 °C,  $\lambda = \lambda p$ , unless otherwise noted)

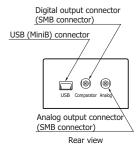
Parameter	Symbol	C11208-150	C11208-350	Unit
Internal MPPC	-	S12576-050	S12577-050	-
Effective photosensitive area	-	1 × 1	3 × 3	mm
Pixel pitch	-	5	60	μm
Number of pixels	-	400	3600	-
Spectral response range	λ	320 t	o 900	nm
Peak sensitivity wavelength	λр	4	50	nm
Element temperature (setting temperature)	Td	-10	0	°C
Photon detection efficiency*	PDE	3	:5	%
Dark count*	-	5	120	kcps
Comparator output	-	TTL cor	mpatible	-
Comparator threshold level	-	9 adjustable levels:	0.5 to 7.5 and disable	p.e.
Interface	-	USE	-	
Dimensions	-	98 × 6	60 × 35	mm

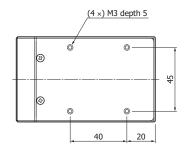
<sup>\*0.5</sup> p.e. (threshold level)

#### Dimensional outline (unit: mm)

# 

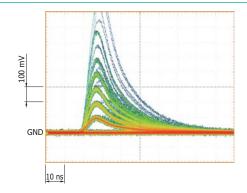




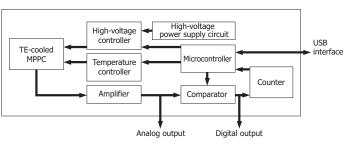


Tolerance unless otherwise noted: ±0.5

#### Analog output waveform



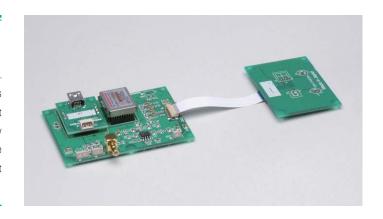
#### Block diagram



KACCC0518EA

# C12332

The C12332 is a starter kit designed for simple non-cooled MPPC evaluations. It consists of a sensor board and a power supply board. The sensor board includes an MPPC socket and a temperature sensor. The power supply board includes a C11204-01 power supply module for MPPC, a signal amplifier circuit, and a USB interface board. The USB interface allows you to change the bias voltage and set the temperature compensation coefficient from a PC. The C12332 operates just by connecting it to an external power supply (±5 V).



(Typ. Ta=25 °C, Vs=±5 V, unless otherwise noted)

Parameter		Symbol	C12332	Unit
Supply voltage		Vs	±5	V
Supply voltage range		Vo	50 to 90	V
Setting voltage error		-	±10	mV
Setting voltage resolution*		-	10	mV
Voltage monitoring error		-	±10	mV
Current monitoring error		-	±0.05	mA
Load resistance		RL	50 or 1k	Ω
Cutoff frequency	High band	- fc	40	MHz
	Low band		DC	
Integrated thermosensor		-	LM94021BIMG (by Texas Instruments)	-
Interface		-	USB 2.0 (Full speed)	-

<sup>\*</sup>When using sample software

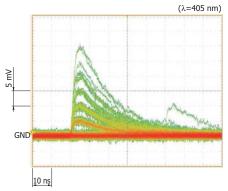
#### Dimensional outline (unit: mm)

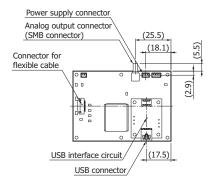
#### Mounting position of MPPC Mounting position of MPPC (S12572-025C/-050C/-100C) (S10985-025C/-050C/-100C) Ħ ٩ Mounting position of MPPC Mounting position of MPPC (S10362-11-025U/-050U/-100U) (S12571-025C/-050C/-100C)

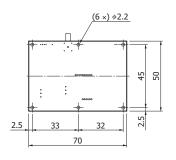
Analog thermosensor Connector for flexible cable 32 37 : (4 ×) ¢2.2 50

Tolerance unless otherwise noted: ±0.2

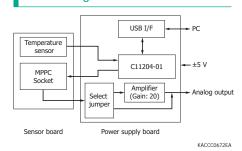
# Analog output waveforms (impulse light)







Tolerance unless otherwise noted: ±0.2 KACCA0315FA



#### **Notice**

- Copies of the full warranty can be obtained prior to the purchase of products by contacting your local Hamamatsu sales office.
- Hamamatsu makes no other warranties, and any and all implied warranties of merchantability, or fitness for a particular purpose, are hereby disclaimed. The customer is responsible for use of the product in accordance with Hamamatsu's instructions and within the operating specifications and ratings listed in this catalogue. Hamamatsu shall not be responsible for the customer's improper selection of a product for a particular application or otherwise. No warranty will apply if the products are in any way altered or modified after delivery by Hamamatsu or for any intentional misuse or abuse of the products. Proper design safety rules should be followed when incorporating these products into devices that could potentially cause bodily injury.
- Hamamatsu's liability on any claim for loss or damage arising out of the supplying of any products, whether based on contract, warranty, tort (including negligence and for property damage or death and bodily injury) or other grounds, shall not in any event exceed the price allocable to such products or a part thereof involved in the claim, regardless of cause or fault. In no event shall Hamamatsu be responsible to the customer or any third party for any consequential, incidental or indirect damages, including but not limited to loss of profits, revenues, sales, data, business, goodwill or use, even if the company has been advised of the possibility of such loss or damage. The limitation of liability set forth herein applies both to products and services purchased or otherwise provided hereunder. This warranty is limited to repair or replacement, at the sole option of Hamamatsu, of any product which is defective in workmanship or materials used in manufacture. All warranty claims must be made within 1 year from the date of purchase or provision of the products or services.
- Products that are amenable to repair shall be done so either under warranty or pursuant to a separate repair agreement. Some products cannot be repaired either because of the nature or age of the product, the unavailability of spare parts, or the extent of the damage is too great. Please contact your local Hamamatsu office for more details.
- The products described in this catalogue should be used by persons who are accustomed to the properties of photoelectronics devices, and have expertise in handling and operating them. They should not be used by persons who are not experienced or trained in the necessary precautions surrounding their use.
- The information in this catalogue is subject to change without prior notice.
- Information furnished by Hamamatsu is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.
- No patent rights are granted to any of the circuits described herein.

# AMAMATSL

#### HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1, Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558, Japan Telephone: (81)53-434-3311, Fax: (81)53-434-5184

www.hamamatsu.com

#### **Main Products**

Si photodiodes APD Photo IC Image sensors X-ray flat panel sensors **PSD** Infrared detectors

**LED** 

Optical communication devices Automotive devices Mini-spectrometers High energy particle/X-ray detectors Opto-semiconductor modules

#### Hamamatsu also supplies:

Photoelectric tubes Imaging tubes Light sources Imaging and processing systems

Information in this catalogue is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein

© 2013 Hamamatsu Photonics K.K.

Quality, technology, and service are part of every product.

#### Sales Offices

JAPAN: HAMAMATSU PHOTONICS K.K. 325-6, Sunayama-cho, Naka-ku Hamamatsu City, 430-8587, Japan Telephone: (81)53-452-2141, Fax: (81)53-456-7889

HAMAMATSU PHOTONICS (CHINA) CO., LTD.
1201 Tower B, Jiaming Center, No.27 Dongsanhuan Beilu,
Chaoyang District, Beijing 100020, China
Telephone: (86)10-6586-6006, Fax: (86)10-6586-2866 E-mail: hpc@hamamatsu.com.cn

# U.S.A.: HAMAMATSU CORPORATION Main Office

Main Office 360 Foothill Road, P.O. BOX 6910, Bridgewater, N.J. 08807-0910, U.S.A. Telephone: (1)908-231-0960, Fax: (1)908-231-1218 E-mail: usa@hamamatsu.com

Western U.S.A. Office: Suite 200, 2875 Moorpark Avenue San Jose, CA 95128, U.S.A. Telephone: (1)408-261-2022, Fax: (1)408-261-2522 E-mail: usa@hamamatsu.com

#### United Kingdom, South Africa: HAMAMATSU PHOTONICS UK LIMITED Main Office

Main Office
2 Howard Court, 10 Tewin Road, Welwyn Garden City,
Hertfordshire AL7 1BW, United Kingdom
Telephone: (44)1707-294888, Fax: (44)1707-325777
E-mail: info@hamamatsu.co.uk

South Africa office: PO Box 1112 Buccleuch 2066 Johannesburg, South Africa Telephone/Fax: (27)11-802-5505

France, Portugal, Belgium, Switzerland, Spain: HAMAMATSU PHOTONICS FRANCE S.A.R.L. 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France Telephone: (33)1 69 53 71 00 Fax: (33)1 69 53 71 10 E-mail: infos@hamamatsu.fr

Swiss Office: Dornacherplatz 7 Dornacnerplatz / 4500 Solothurn, Switzerland Telephone: (41)32/625 60 60, Fax: (41)32/625 60 61 E-mail: swiss@hamamatsu.ch

Belgium Office: Axisparc Technology , rue Andre Dumont 7 - 1435 Mont-Saint-Guibert, Belgium Telephone: (32)10 45 63 34 Fax: (32)10 45 63 67 E-mail: infoweb@hamamatsu.be

Spanish Office: C. Argenters, 4 edif 2 C. Agenters, 4 et al. 2 Parque Tecnologico del Valles E-08290 CERDANYOLA, (Barcelona) Spain Telephone: (34)93 582 44 30 Fax: (34)93 582 44 31 E-mail: infospain@hamamatsu.es

Germany, Denmark, Netherlands, Poland: HAMAMATSU\_PHOTONICS\_DEUTSCHLAND\_GmbH Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany Telephone: (49)8152-375-0, Fax: (49)8152-265-8 E-mail: info@hamamatsu.de





Danish Office: Lautruphoj 1-3 DK-2750 Ballerup, Denmark Telephone: (45)70 20 93 69, Fax: (45)44 20 99 10 E-mail: info@hamamatsu.de

Netherlands Office: Televisieweg 2 NL-1322 AC Almere, The Netherlands Telephone: (31)36-5405384, Fax: (31)36-5244948

E-mail: info@hamamatsu.nl

Poland Office: 02-525 Warsaw, St. A. Boboli Str., Poland Telephone: (48)22-646-0016, Fax: (48)22-646-0018 E-mail: jbaszak@hamamatsu.de

#### North Europe and CIS: HAMAMATSU PHOTONICS NORDEN AB Main Office

Torshamnsgatan 35 16440 Kista, Sweden Telephone: (46)8-509-031-00, Fax: (46)8-509-031-01 E-mail: info@hamamatsu.se

Russian Office: Vyatskaya St. 27, bld. 15 Kosmodamianskaya nab. 52/1, 14th floor RU-127015 Moscow, Russia Telephone: (7) 495 258 85 18, Fax: (7) 495 258 85 19 E-mail: info@hamamatsu.ru

#### HAMAMATSU PHOTONICS ITALIA S.R.L.

Strada della Moia, 1 int. 6 20020 Arese, (Milano), Italy Telephone: (39)02-935 81 733 Fax: (39)02-935 81 741 E-mail: info@hamamatsu.it

Rome Office: Viale Cesare Pavese, 435 700144 Roma, Italy Telephone: (39)06-50513454, Fax: (39)06-50513460 E-mail: inforoma@hamamatsu.it

#### Taiwan

HAKUTO TAIWAN LTD. 6F, No.308, Pa teh Road, Sec, 2, Taipei, Taiwan R.O.C. Telephone: (886)2-8772-8910 Fax: (886)2-8772-8918

KORYO ELECTRONICS CO., LTD. 9F-7, No. 79, Hsin Tai Wu Road Sec.1, Hsi-Chih, Taipei, Taiwan, R.O.C. Telephone: (886)2-2698-1143, Fax: (886)2-2698-1147

Republic of Korea: SANGKI CORPORATION Suite 431, World Vision BLDG. 24-2 Yoido-Dong Youngdeungpo-Ku Seoul, 150-877 Telephone: (82)2-780-8515 Fax: (82)2-784-6062

HAKUTO SINGAPORE PTE LTD.

Block 2, Kaki Bukit Avenue 1, #04-01 to #04-04 Kaki Bukit Industrial Estate, Singapore 417938 Telephone: (65)67458910, Fax: (65)67418200